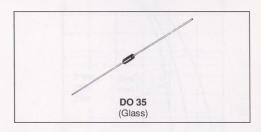


SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

Metal to silicon junction diode featuring high breakdown, low turn-on voltage and ultrafast switching. Primarly intended for high level UHF/VHF detection and pulse application with broad dynamic range. Matched batches are available on request.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit	
V _{RRM}	Repetitive Peak Reverse Voltage	70		
l _F	Forward Continuous Current*	T _a = 25°C	15	mA
Ptot	Power Dissipation*	T _a = 25°C	430	mW
T _{stg} T _j	Storage and Junction Temperature Range		- 65 to 200	°C
TL	Maximum Lead Temperature for Soldering during from Case	230	°C	

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th (j-a)}	Junction-ambient*	400	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol		Test Conditions	Min.	Typ.	Max.	Unit
V (BR)	T _{amb} = 25°C	$I_{R} = 10\mu A$	70			٧
V _F **	T _{amb} = 25°C	I _F = 1mA			0.41	V
	T _{amb} = 25°C	I _F = 15mA			1	
l _B **	T _{amb} = 25°C	V _R = 50V			0.2	μА

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
С	T _{amb} = 25°C	$V_R = 0V$	f = 1MHz			2	pF
τ	T _{amb} = 25°C	$I_F = 5mA$	Krakauer Method			100	ps

On infinite heatsink with 4mm lead length

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

Pulse test: t₀ ≤ 300μs δ < 2%.

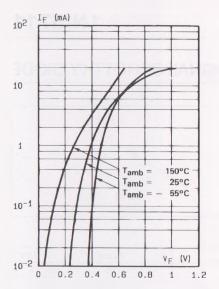


Fig.1 — Forward current versus forward voltage at low level (typical values).

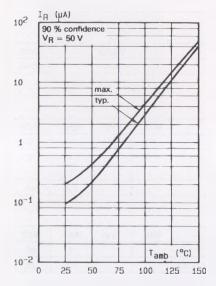


Fig.3 - Reverse current versus ambient temperature.

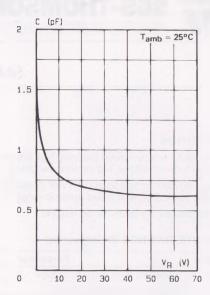


Fig.2 - Capacitance C versus reverse applied voltage $v_{\hat{H}}$ (typical values).

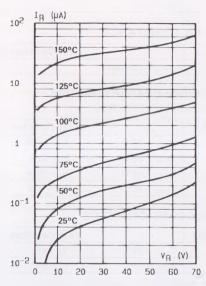


Fig.4 — Reverse current versus continuous reverse voltage (typical values).